



### Low voltage fast-switching NPN power bipolar transistor

**Preliminary Data** 

### **General features**

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-89 plastic package for surface mounting circuits
- In compliance with the 2002/93/EC European Directive

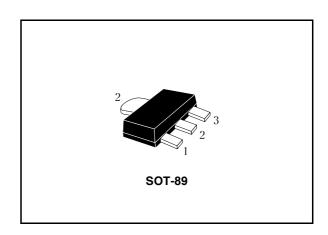
### Description

The device in a NPN transistor manufactured using new "PB-HCD" (Power Bipolar High Current Density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

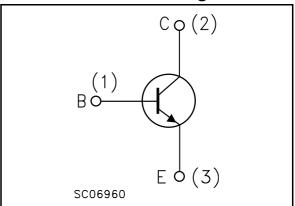
The complementary PNP is the 2STF2340.

### **Applications**

- LED
- Motherboard & hard disk drive
- Mobile equipment
- Battery charger
- Voltage regulation



### Internal schematic diagram



#### **Order codes**

Part Number	Marking	Package	Packing
2STF1340	1340	SOT-89	Tape & reel

## **Contents**

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2STF1340 Electrical ratings

# 1 Electrical ratings

Table 1. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>CE</sub> = 0)	40	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	40	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	5	V
I <sub>C</sub>	Collector current	3	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5ms)	6	Α
P <sub>tot</sub>	Total dissipation at T <sub>amb</sub> = 25°C	1.4	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thj-amb</sub> <sup>(1)</sup>	Thermal resistance junction-amb max	89.3	°C/W

<sup>(1)</sup> Device mounted on PCB area of  $1\,\mathrm{cm}^2$ 

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Electrical characteristics 2STF1340

## 2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$ 

Table 3. Electrical characteristics

Symbol	Parameter	Test Condition	ons Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> =0)	V <sub>CB</sub> = 40V			0.1	μА
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> =0)	V <sub>EB</sub> = 5V			0.1	μА
V <sub>(BR)CBO</sub>	Collector-emitter breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 100μA	40			V
V <sub>(BR)CEO</sub> (2)	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10mA	40			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 100μA	5			V
V <sub>CE(sat)</sub> (2)	Collector-emitter saturation voltage	$I_C = 2A$ $I_B = 1$ $I_C = 3A$ $I_B = 1$	100mA 150mA	0.2 0.3		V V
V <sub>BE(sat)</sub> (2)	Base-emitter saturation voltage	I <sub>C</sub> = 2A I <sub>B</sub> =	100mA	0.9	1.25	V
h <sub>FE</sub> <sup>(2)</sup>	DC current gain	$\begin{split} I_{\text{C}} &= 0.1 \text{A} & V_{\text{CE}} \\ I_{\text{C}} &= 1 \text{A} & V_{\text{CE}} \\ I_{\text{C}} &= 3 \text{A} & V_{\text{CE}} \end{split}$	= 2V	280 250 200		
f <sub>T</sub>	Transition frequency	$I_C = 0.1A$ $V_{CE}$ f = 100MHz	= 5V 100			MHz
C <sub>CBO</sub>	Collector-base capacitance	$I_E = 0$ $V_{CB} = 1$	= 10V	tbd		pF
t <sub>on</sub> t <sub>off</sub>	Resistive load Turn-on time Turn-off time	$I_C = 1.5A$ $V_{CC} = I_{B1} = -I_{B2} = 150mA$	= 10V	tbd tbd		ns ns

Note (2) Pulsed duration = 300  $\mu s$ , duty cycle  $\leq 1.5\%$ 

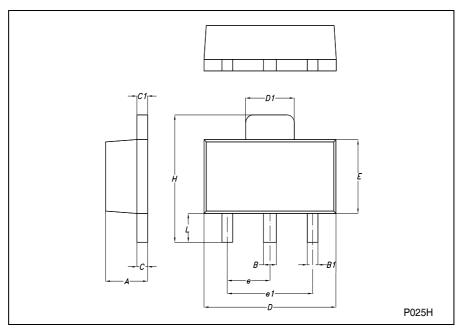
## 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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### **SOT-89 MECHANICAL DATA**

DIM.		mm			mils		
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	1.4		1.6	55.1		63.0	
В	0.44		0.56	17.3		22.0	
B1	0.36		0.48	14.2		18.9	
С	0.35		0.44	13.8		17.3	
C1	0.35		0.44	13.8		17.3	
D	4.4		4.6	173.2		181.1	
D1	1.62		1.83	63.8		72.0	
E	2.29		2.6	90.2		102.4	
е	1.42		1.57	55.9		61.8	
e1	2.92		3.07	115.0		120.9	
Н	3.94		4.25	155.1		167.3	
L	0.89		1.2	35.0		47.2	



2STF1340 Revision history

## 4 Revision history

Table 4. Revision history

Date	Revision	Changes
20-Oct-2006	1	Initial release.

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